

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A thin-film semiconductor device comprising:  
a first plurality of thin-film transistors having different driving voltages than a second plurality of thin-film transistors, wherein said first and second plurality of transistors are formed on a glass substrate,

wherein an electric field of a gate ~~electrode~~ insulator at each of said driving voltages of said first and second plurality of thin-film transistors is in a range of about 1MV/cm to 2MV/cm, and a drain concentration of P-type thin-film transistors is in a range of about  $3\text{E}+19/\text{cm}^3$  to  $1\text{E}+20/\text{cm}^3$ .

2. (original): The thin-film semiconductor device according to claim 1,  
wherein said first plurality of thin-film transistors comprising N-type and P-type thin-film transistors have a lower driving voltage than said second plurality of thin-film transistors comprising N-type and P-type thin film transistor.

3. (original): The thin-film semiconductor device according to claim 1,  
wherein a plurality of gate insulating films of said first and second plurality of thin-film transistors have substantially the same thickness.

4. (original): The thin-film semiconductor device according to claim 2, wherein at least one N-type thin-film transistor of said second plurality of thin-film transistors have a lightly-doped drain structure.

5. (currently amended): A thin-film semiconductor device comprising:  
a first plurality of thin-film transistors having different driving voltages than a second plurality of thin-film transistors, wherein said first and second plurality of transistors are formed on a glass substrate,  
wherein an electric field of a gate ~~electrode~~ insulator at each of said driving voltages of said first and second plurality of thin-film transistors is in a range of about 0.2MV/cm to 0.8MV/cm, and a drain concentration of P-type thin-film transistors is in a range of about  $3\text{E}+19/\text{cm}^3$  to  $1\text{E}+20/\text{cm}^3$ .

6. (original): The thin-film semiconductor device according to claim 5, wherein said first and second plurality of thin-film transistors comprising N-type and P-type thin-film transistors have a lower driving voltage than said second plurality of thin-film transistors comprising N-type and P-type thin film transistor.

7. (original): The thin-film semiconductor device according to claim 5, wherein a plurality of gate insulating films of said first and second plurality of thin-film transistors has substantially the same thickness.

8. (original): The thin-film semiconductor device according to claim 6, wherein at least one N-type thin-film transistor of said second plurality of thin-film transistors have a lightly-doped drain structure.

**Claims 9-12 (canceled).**

13. (original): A liquid crystal display comprising:  
a thin-film semiconductor device according to claim 1; and  
a driver circuit.

**Claim 14 (canceled).**

15. (withdrawn): A thin-film semiconductor device manufacturing method comprising:  
providing a glass substrate  
forming a plurality of gate insulating films of a plurality of thin-film transistors, wherein said gate insulating films are formed so as to have a substantially the same thickness, and  
wherein said plurality of thin-film transistors have different driving voltages.

16. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 15,  
wherein said gate insulating films are formed at substantially the same time.

17. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 15, further comprising:

forming source/drain regions of a plurality of P-type thin-film transistors having different driving voltages.

18. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 15, further comprising:

forming source/drain regions of a plurality of N-type thin-film transistors having different driving voltages.

19. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 17, wherein said source/drain regions are formed at substantially the same time.

20. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 18,

wherein said source/drain regions are formed at substantially the same time.

21. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 18, further comprising:

forming Lightly-doped drain structure on at least one part of the N-type thin-film transistors.